Abstracts

UHF High-Power Low-Distortion Transistor Amplifier with High-Dielectric (epsilon/sub r/=39) Substrate

Y. Kajiwara, T. Noguchi, T. Sugiura, H. Takamizawa, K. Hirakawa and K. Sasaki. "UHF High-Power Low-Distortion Transistor Amplifier with High-Dielectric (epsilon/sub r/=39) Substrate." 1979 MTT-S International Microwave Symposium Digest 79.1 (1979 [MWSYM]): 332-334.

A hybrid-integrated UHF power amplifier has been designed and fabricated on high-dielectric (epsilon/sub r/=39) substrate. The amplifier was developed to replace TWTs in television transposers and provides a rated output peak power of 32W with low-distortion characteristic over the 650%~770 MHz frequency range.

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